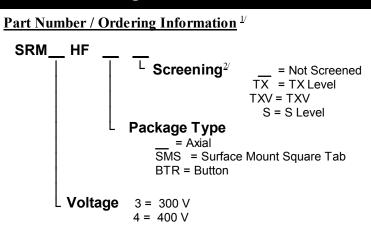


Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, Ca 90638 Phone: (562) 404-4474 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

Designer's Data Sheet



SRM3HF thru SRM4HF Series

20 AMP 300-400 Volts 40 nsec Hyper Fast Rectifier

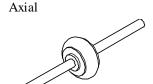
Features:

- Replaces DO-4 and DO-5 (1N5816,1N6306)
- High Current/ Voltage Version of 1N5811
- Hyper Fast Recovery
- PIV to 400 Volts
- Low Reverse Leakage Current
- Hermetically Sealed Void-Free Construction^{3/}
- Monolithic Single Chip Construction
- High Surge Rating
- Low Thermal Resistance
- Available in Surface Mount Versions
- Equivalent to 1N6688-1N6689
- TX, TXV, and Space Level Screening Available

MAXIMUM RATINGS		Symbol	Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage	SRM3HF SRM4HF	V	300 400	Volts
Average Rectified Forward Current (Resistive Load, 60Hz Sine Wave, TA=25°C)		l _o 20		Amps
Peak Surge Current (8.3 ms Pulse, Half sine Wave Superimposed on le Pulses, T _A =25°C)	s Pulse, Half sine Wave Superimposed on lo, Allow Junction to Reach Equilibrium Between		475	Amps
Operating and Storage Temperature		T _{op} & T _{stg} -65 to +175		°C
Maximum Thermal Resistance (Axial – Junction to Lead, L=3/8") (SMS – Junction to End Tab) (Button – Junction to Case)	Axial() Square Tab (SMS) Button (BTR)		3.0 2.5 1.0	°C/W

Notes

- 1/ For ordering information, price, operating curves, and availability, contact factory.
- 2/ Modified MIL-PRF-19500 Screening Flow Consult Factory.
- 3/ PIND testing not required on void free devices per MIL-PRF-19500.









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ELECTRICAL CHARACTERISTICS		Symbol	Max	Unit
Instantaneous Forward Voltage Drop (I _F = 20Adc, 500 µsec Pulse, T _A = 25°C)		V_{F1}	1.05	Vdc
Instantaneous Forward Voltage Drop (I _F = 20Adc, 300 µsec Pulse, T _A = -65°C)		V _{F2}	1.2	Vdc
Reverse Leakage Current (Rated V _R , 300 μsec Pulse Minimum, T _A = 25°C)		I _{R1}	100	μΑ
Reverse Leakage Current (Rated V _R , 300 μsec Pulse Minimum, T _A = 100°C)		I _{R2}	10	mA
Junction Capacitance $(V_R = 10 \ V_{DC}, f = 1 MHz, T_A = 25^{\circ}C)$		CJ	350	pF
Reverse Recovery Time (I _F = 0.5A, I _R = 1.0 A, I _{RR} = 0.25A, T _A = 25°C)		t _{rr}	40	nsec

